

65V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
65V	18mΩ @ V _{GS} = 10V	8.1A
037	$23m\Omega$ @ $V_{GS} = 4.5V$	7.1A

Features and Benefits

- 100% Unclamped Inductive Switching (UIS) Test in Production— Ensures More Reliable and Robust End Application
- 0.6mm Profile—Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low On-Resistance
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

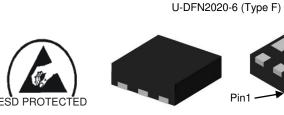
Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

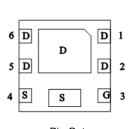
- DC-DC Converter
- Adaptor Switch
- Wireless Charging

Mechanical Data

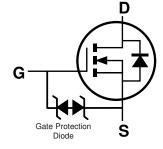
- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.007 grams (Approximate)







Pin Out **Bottom View**



Internal Schematic

Ordering Information (Note 4)

Part Number	Package	Quantity per Reel		
DMT6017LFDF-7	U-DFN2020-6 (Type F)	3,000		
DMT6017LFDF-13	U-DFN2020-6 (Type F)	10,000		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



T17 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 9 = 2019)

W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key										
Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	
Code	9	0	1	2	3	4	5	6	7	
							1			
Week	1-26			27-52				53		
Code	A-Z			a-z			Z			
							•			
Internal Code	Sun	Mon		Tue	Wed	Thu		Fri	Sat	
Code	T	U		V	W	X		Υ	Z	



Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	65	V
Gate-Source Voltage	V _{GSS}	±16	V
Continuous Drain Current (Note 6) V _{GS} = 10V	I _D	8.1 6.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	I _{DM}	50	Α
Maximum Body Diode Continuous Current	I _S	8	Α
Pulsed Body Diode Forward Current (10µs Pulse, D	I _{SM}	50	Α
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	19	Α
Avalanche Energy (Note 7) L = 0.1mH	E _{AS}	18	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P _D	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)		R _{OJA}	157	°C/W
Total Power Dissipation (Note 6)	P_{D}	1.76	W	
Thermal Resistance, Junction to Ambient (Note 6)	R _{OJA}	71	°C/W	
Thermal Resistance, Junction to Case (Note 6)	R _{eJC}	10	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

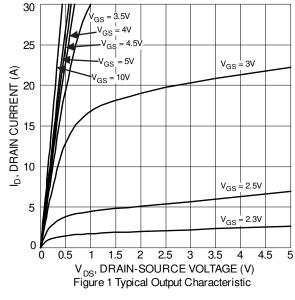
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 8)								
Drain-Source Breakdown Voltage	BV _{DSS}	65	_	_	V	$V_{GS} = 0V, I_{D} = 10mA$		
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	V _{DS} = 48V, V _{GS} = 0V		
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 12.8V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 8)	0 100 1 100 1 20 1							
Gate Threshold Voltage	V _{GS(TH)}	1	1.4	2.3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$		
Static Drain-Source On-Resistance	р	_	13.2	18	mΩ	$V_{GS} = 10V, I_D = 6A$		
Static Drain-Source Off-Nesistance	R _{DS(ON)}	_	17	23	11177	$V_{GS} = 4.5V, I_D = 4A$		
Diode Forward Voltage	V_{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1A$		
DYNAMIC CHARACTERISTICS (Note 9)								
Input Capacitance	Ciss		891	_		V _{DS} = 30V, V _{GS} = 0V, f = 1MHz		
Output Capacitance	Coss		223	_	pF			
Reverse Transfer Capacitance	Crss	1	29	_				
Gate Resistance	R_g		1.57	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$		
Total Gate Charge (V _{GS} = 4.5V)	Q_g	_	7.5	_		V 00V I 0A		
Total Gate Charge (V _{GS} = 10V)	Q_g		15.3	_	nC			
Gate-Source Charge	Q_{gs}		1.8	_	110	$V_{DS} = 30V$, $I_D = 6A$		
Gate-Drain Charge	Q_{gd}	_	3.1	_				
Turn-On Delay Time	t _{D(ON)}	_	4.0	_		V _{GS} = 10V, V _{DS} = 30V,		
Turn-On Rise Time	t _R	_	5.9	_				
Turn-Off Delay Time	t _{D(OFF)}		11.7	_	ns	$R_g = 3.3\Omega$, $I_D = 6A$		
Turn-Off Fall Time	t _F		3.3					
Body Diode Reverse Recovery Time	t _{RR}	_	21.1	_	ns	L CA di/dt 1000/		
Body Diode Reverse Recovery Charge	Q _{RR}		11.9	_	nC	$I_F = 6A$, $di/dt = 100A/\mu s$		

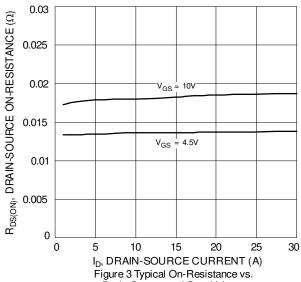
Notes:

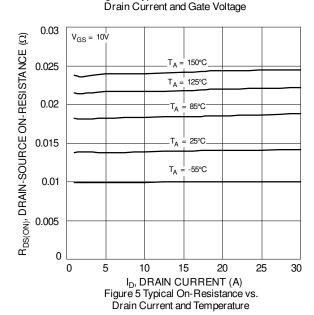
- 5. Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout. 6. Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
- I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

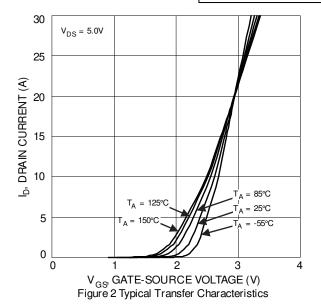


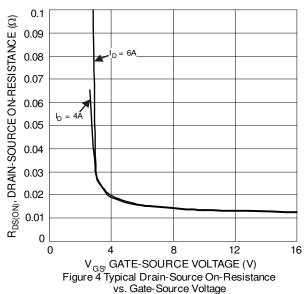








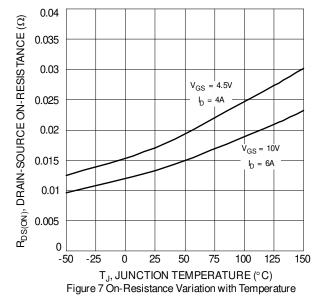


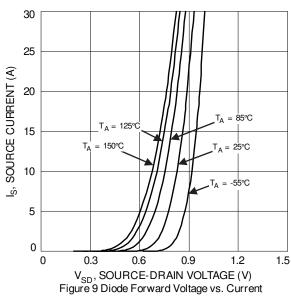


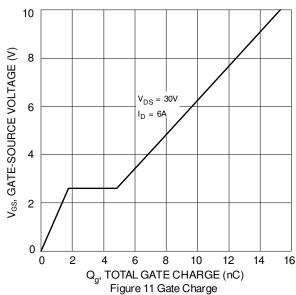
2.4 2.2 R_{DS(ON)}, DRAIN-SOURCE ON-RESISTANCE (NO RMALIZED) 2 1.8 $V_{GS} = 4.5$ 1.6 1.4 10V V_{GS} = 1.2 $I_D = 6A$ 1 8.0 0.6 0.4 -50 25 50 75 100 125 T_J, JUNCTION TEMPERATURE (°C)

Figure 6 On-Resistance Variation with Temperature









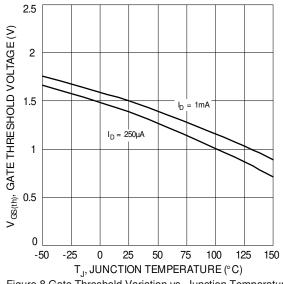
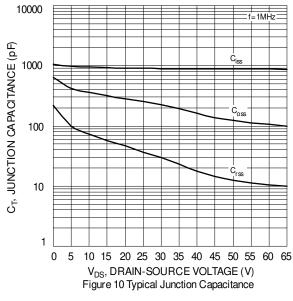
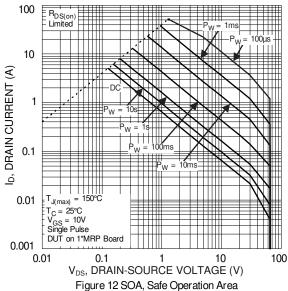
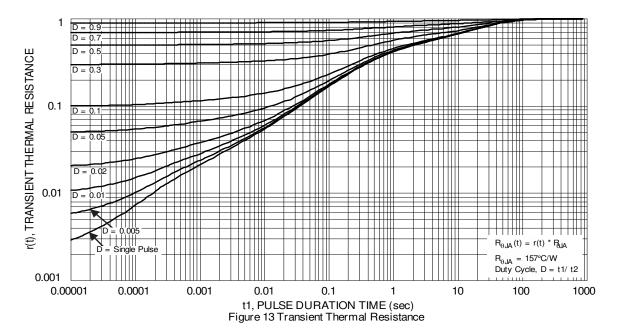


Figure 8 Gate Threshold Variation vs. Junction Temperature







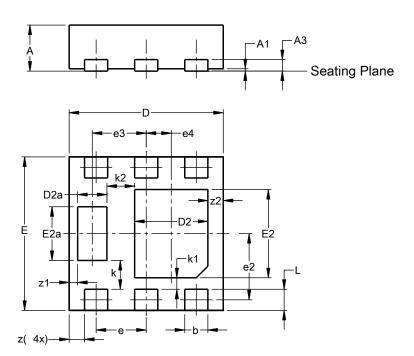




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

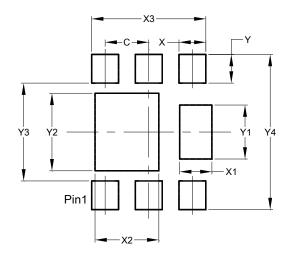


U-DFN2020-6							
(Type F)							
Dim	Min	Min Max Typ					
Α	0.57	0.63	0.60				
A 1	0.00	0.05	0.03				
А3	-	1	0.15				
b	0.25	0.35	0.30				
D	1.95	2.05	2.00				
D2	0.85	1.05	0.95				
D2a	0.33	0.43	0.38				
Е	1.95	2.05	2.00				
E2	1.05	1.25	1.15				
E2a	0.65	0.75	0.70				
е	0.65 BSC						
e2	0.863 BSC						
е3		0.70 BS	С				
e4	0.325 BSC						
k	0.37 BSC						
k1	0.15 BSC						
k2	0.36 BSC						
L	0.225 0.325 0.275						
Z	0.20 BSC						
z1	0.110 BSC						
z2	0.20 BSC						
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value
Dilliensions	(in mm)
С	0.650
Х	0.400
X1	0.480
X2	0.950
Х3	1.700
Υ	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2019, Diodes Incorporated

www.diodes.com